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ABSTRACT OF THE DISCLOSURE

Dry etching of a metal oxide film exposed without being coated with a photoresist is carried out with plasma of a gas obtained by mixing hydrogen iodide with at least one gas selected from the group consisting of a group consisting of fluorine gas and fluorine-based compound gases and a group consisting of nitrogen gas and nitrogen-based compound gases, and then after the exposing of the above mentioned photoresist film to plasma of oxygen gas, the remaining photoresist film is removed by etching with plasma of a gas obtained by mixing oxygen gas with at least one gas selected from the group consisting of a group consisting of fluorine gas and fluorine-based compound gases and a group consisting of nitrogen gas and nitrogen-based compound gases. Volume flow rate conditions of hydrogen iodide gas or oxygen gas and the gas selected from the group consisting of a group consisting of fluorine gas and fluorine-based compound gases and a group consisting of nitrogen gas and nitrogen-based compound gases are prescribed in specific ranges.

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